

NESG3033M14

NPN SiGe RF Transistor for Low Noise, High-Gain Amplification 4-Pin Lead-Less Minimold (M14, 1208 PKG)

R09DS0049EJ0300

Rev.3.00

Sep 14, 2012

FEATURES

- The NESG3033M14 is an ideal choice for low noise, high-gain amplification
NF = 0.6 dB TYP. @ $V_{CE} = 2\text{ V}$, $I_C = 6\text{ mA}$, $f = 2.0\text{ GHz}$
- Maximum stable power gain: MSG = 20.5 dB TYP. @ $V_{CE} = 2\text{ V}$, $I_C = 15\text{ mA}$, $f = 2.0\text{ GHz}$
- SiGe HBT technology (UHS3) adopted: $f_{max} = 110\text{ GHz}$
- This product is improvement of ESD of NESG3032M14.
- 4-pin lead-less minimold (M14, 1208 PKG)

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ORDERING INFORMATION

Part Number	Order Number	Package	Quantity	Supplying Form
NESG3033M14	NESG3033M14-A	4-pin lead-less minimold (M14, 1208 PKG) (Pb-Free)	50 pcs (Non reel)	8 mm wide embossed taping - Pin 1 (Collector), Pin 4 (NC) face the perforation side of the tape
NESG3033M14-T3	NESG3033M14-T3-A		10 kpcs/reel	

Remark To order evaluation samples, please contact your nearby sales office.
Unit sample quantity is 50 pcs.

ABSOLUTE MAXIMUM RATINGS ($T_A = +25^\circ\text{C}$)

Parameter	Symbol	Ratings	Unit
Collector to Base Voltage	V_{CBO} Note 1	5.0	V
Collector to Emitter Voltage	V_{CEO}	4.3	V
Base Current	I_B Note 1	12	mA
Collector Current	I_C	35	mA
Total Power Dissipation	P_{tot} Note 2	150	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-65 to +150	$^\circ\text{C}$

Notes 1. V_{CBO} and I_B are limited by the permissible current of the protection element.

2. Mounted on $1.08\text{ cm}^2 \times 1.0\text{ mm}$ (t) glass epoxy PWB

CAUTION

Observe precautions when handling because these devices are sensitive to electrostatic discharge.

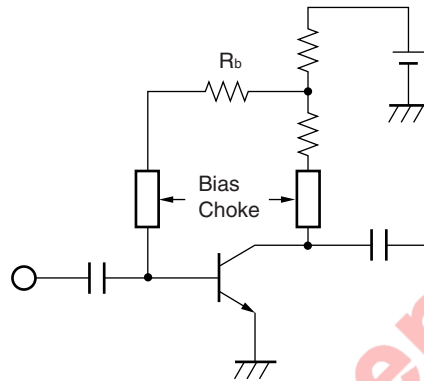
The mark <R> shows major revised points.

The revised points can be easily searched by copying an "<R>" in the PDF file and specifying it in the "Find what:" field.

RECOMMENDED OPERATING RANGE ($T_A = +25^{\circ}\text{C}$)

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Input Power	P_{in}	—	—	0	dBm
Base Feedback Resister	R_b	—	—	100	$k\Omega$

Remark When the voltage return bias circuit like the figure below is used, a current increase is seen because the ESD protection element is turned on when recommended range of motion in the above table is exceeded. However, there is no influence of reliability, including deterioration.



Not recommended
for new design

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ELECTRICAL CHARACTERISTICS (T_A = +25°C)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
DC Characteristics						
Collector Cut-off Current	I _{CBO}	V _{CB} = 5 V, I _E = 0	–	–	100	nA
Emitter Cut-off Current	I _{EBO}	V _{EB} = 1 V, I _C = 0	–	–	100	nA
DC Current Gain	h _{FE} ^{Note 1}	V _{CE} = 2 V, I _C = 6 mA	220	300	380	–
RF Characteristics						
Insertion Power Gain	S _{21e} ²	V _{CE} = 2 V, I _C = 15 mA, f = 2.0 GHz	15.0	17.5	–	dB
Noise Figure	NF	V _{CE} = 2 V, I _C = 6 mA, f = 2.0 GHz, Z _S = Z _{Sopt} , Z _L = Z _{Lopt}	–	0.60	0.85	dB
Associated Gain	G _a	V _{CE} = 2 V, I _C = 6 mA, f = 2.0 GHz, Z _S = Z _{Sopt} , Z _L = Z _{Lopt}	–	17.5	–	dB
Reverse Transfer Capacitance	C _{re} ^{Note 2}	V _{CB} = 2 V, I _E = 0, f = 1 MHz	–	0.15	0.25	pF
Maximum Stable Power Gain	MSG ^{Note 3}	V _{CE} = 2 V, I _C = 15 mA, f = 2.0 GHz	17.5	20.5	–	dB
Gain 1 dB Compression Output Power	P _O (1 dB)	V _{CE} = 3 V, I _C (set) = 20 mA, f = 2.0 GHz, Z _S = Z _{Sopt} , Z _L = Z _{Lopt}	–	12.5	–	dBm
3rd Order Intermodulation Distortion Output Intercept Point	OIP ₃	V _{CE} = 3 V, I _C (set) = 20 mA, f = 2.0 GHz, Z _S = Z _{Sopt} , Z _L = Z _{Lopt}	–	24.0	–	dBm

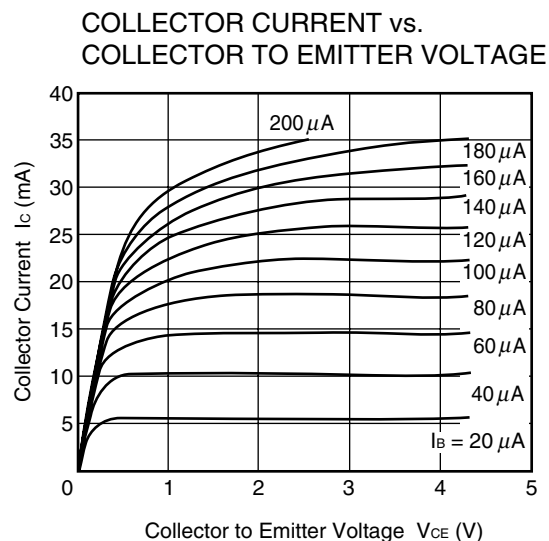
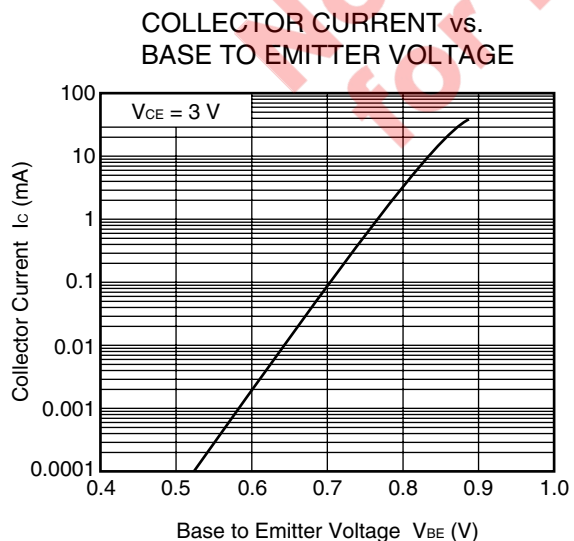
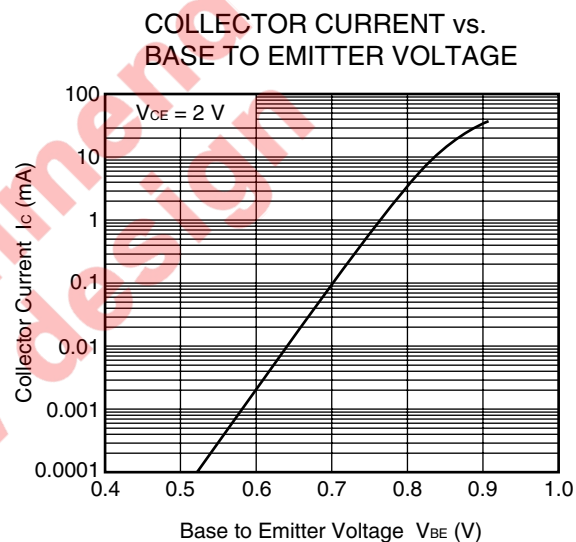
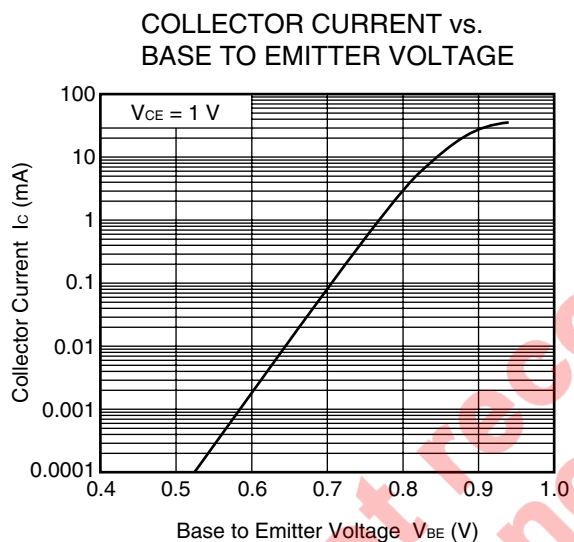
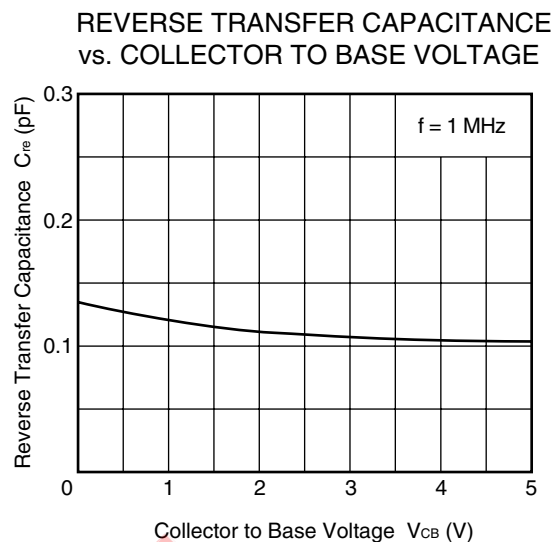
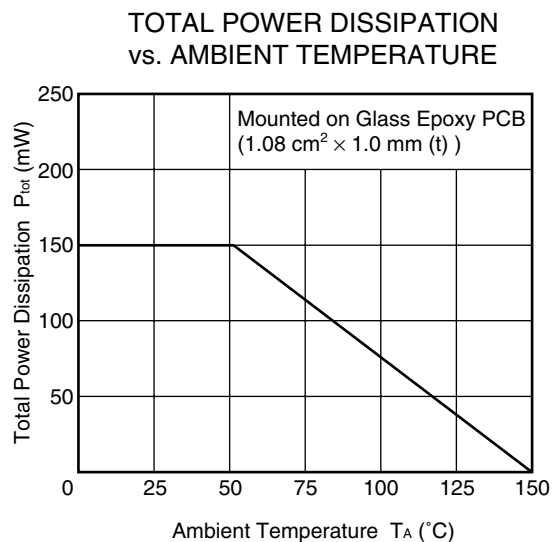
Notes 1. Pulse measurement: PW ≤ 350 μs, Duty Cycle ≤ 2%**2.** Collector to base capacitance when the emitter grounded

$$\mathbf{3. \text{ MSG} = \left| \frac{S_{21}}{S_{12}} \right|}$$

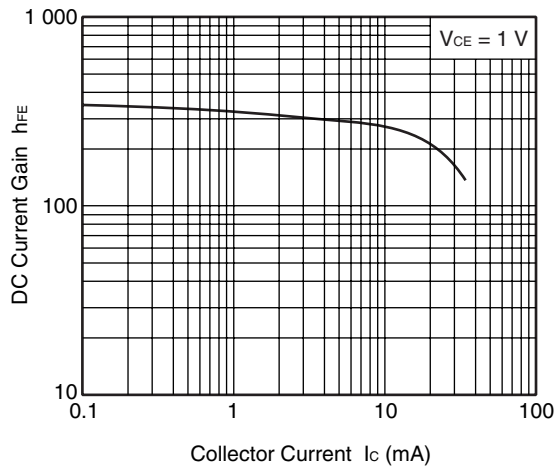
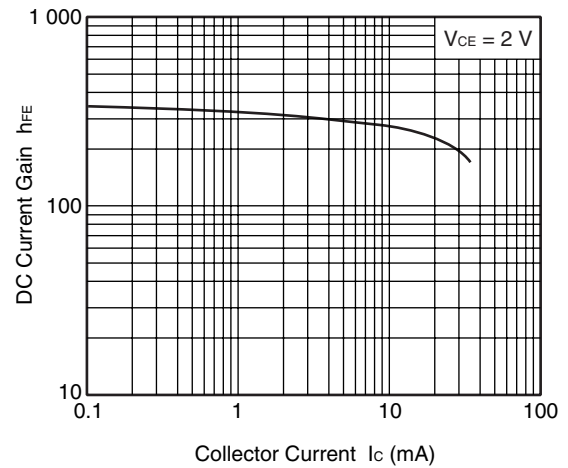
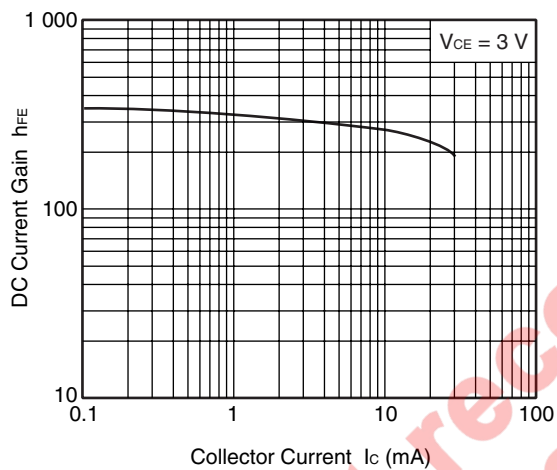
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h_{FE} CLASSIFICATION

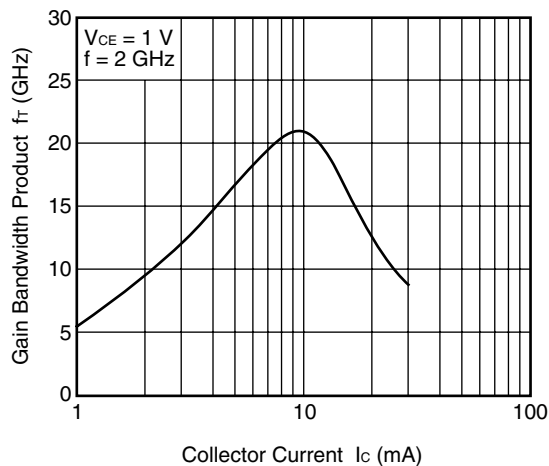
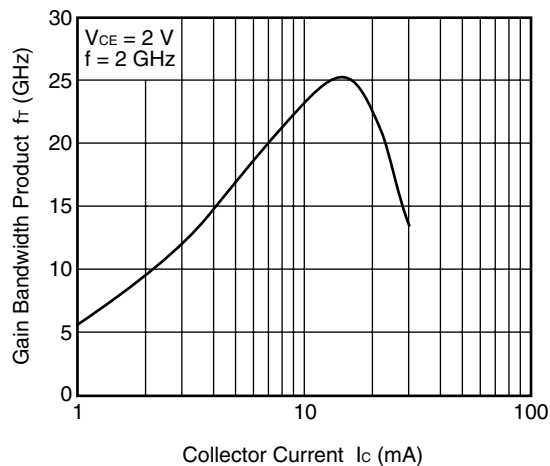
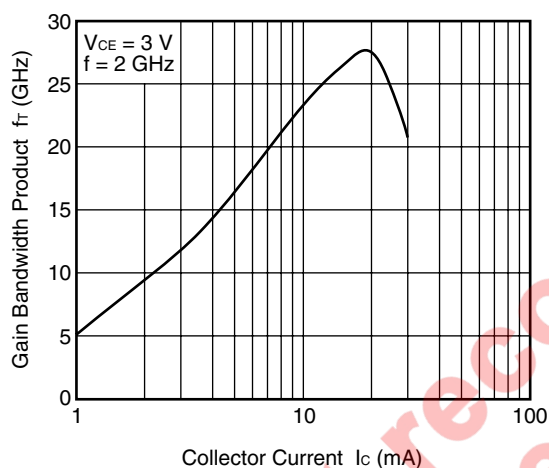
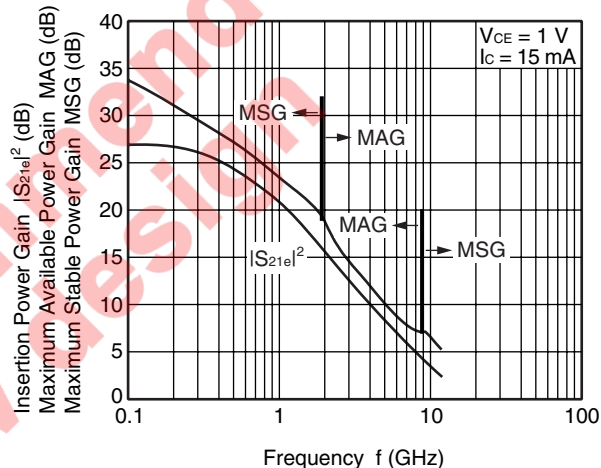
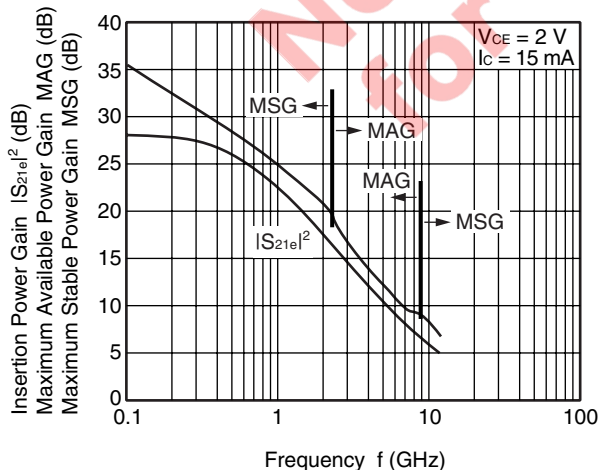
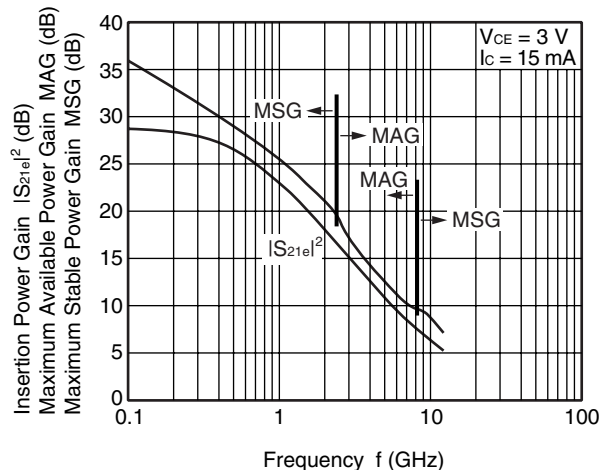
Rank	FB/YFB
Marking	zL
h _{FE} Value	220 to 380

TYPICAL CHARACTERISTICS ($T_A = +25^\circ\text{C}$, unless otherwise specified)

Remark The graphs indicate nominal characteristics.

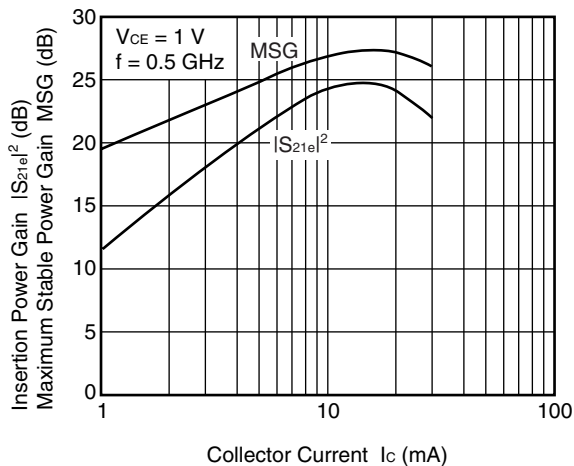
DC CURRENT GAIN vs.
COLLECTOR CURRENTDC CURRENT GAIN vs.
COLLECTOR CURRENTDC CURRENT GAIN vs.
COLLECTOR CURRENT

Remark The graphs indicate nominal characteristics.

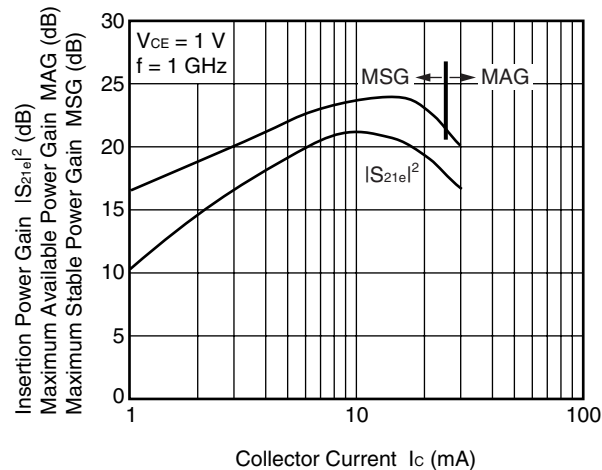
GAIN BANDWIDTH PRODUCT
vs. COLLECTOR CURRENTGAIN BANDWIDTH PRODUCT
vs. COLLECTOR CURRENTGAIN BANDWIDTH PRODUCT
vs. COLLECTOR CURRENTINSERTION POWER GAIN,
MAG, MSG vs. FREQUENCYINSERTION POWER GAIN,
MAG, MSG vs. FREQUENCYINSERTION POWER GAIN,
MAG, MSG vs. FREQUENCY

Remark The graphs indicate nominal characteristics.

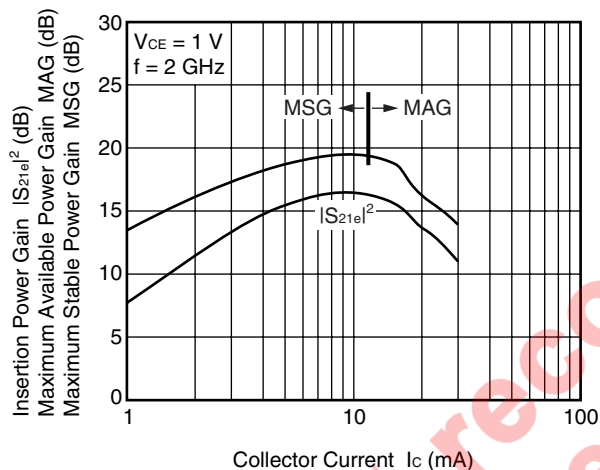
INSERTION POWER GAIN, MSG
vs. COLLECTOR CURRENT



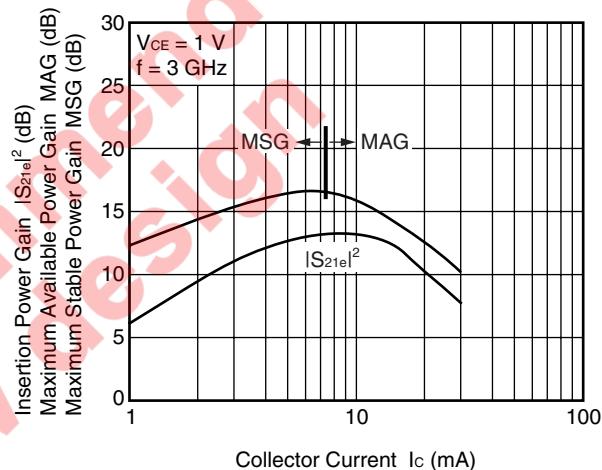
INSERTION POWER GAIN, MAG, MSG
vs. COLLECTOR CURRENT



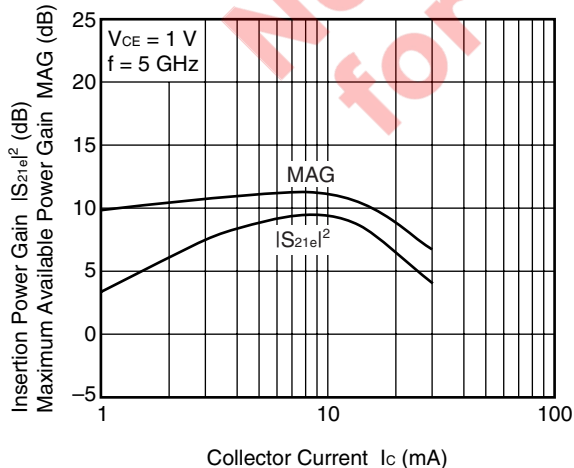
INSERTION POWER GAIN, MAG, MSG
vs. COLLECTOR CURRENT



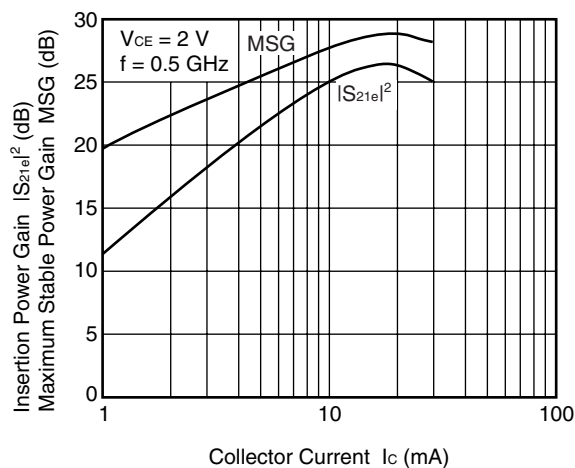
INSERTION POWER GAIN, MAG, MSG
vs. COLLECTOR CURRENT



INSERTION POWER GAIN, MAG
vs. COLLECTOR CURRENT

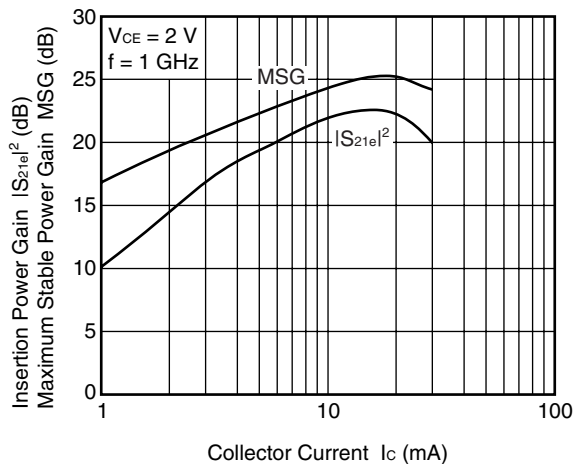


INSERTION POWER GAIN, MSG
vs. COLLECTOR CURRENT

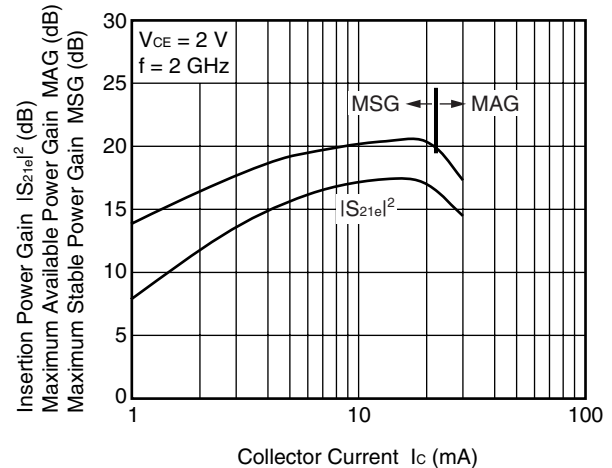


Remark The graphs indicate nominal characteristics.

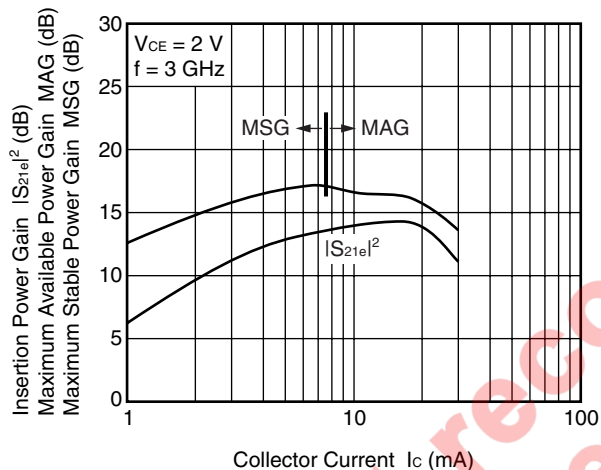
INSERTION POWER GAIN, MSG
vs. COLLECTOR CURRENT



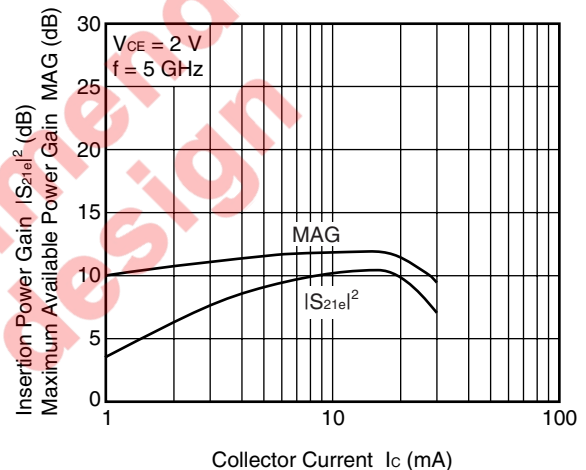
INSERTION POWER GAIN, MAG, MSG
vs. COLLECTOR CURRENT



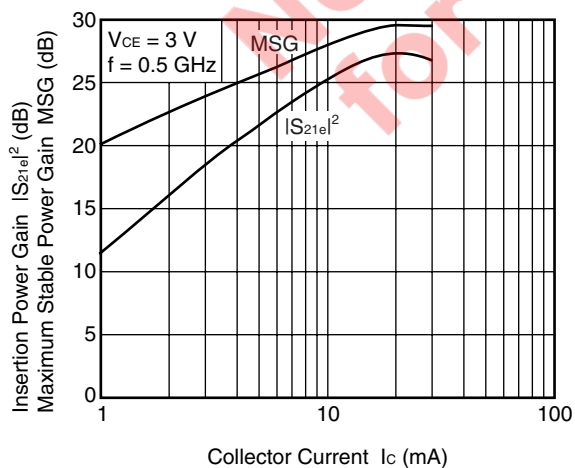
INSERTION POWER GAIN, MAG, MSG
vs. COLLECTOR CURRENT



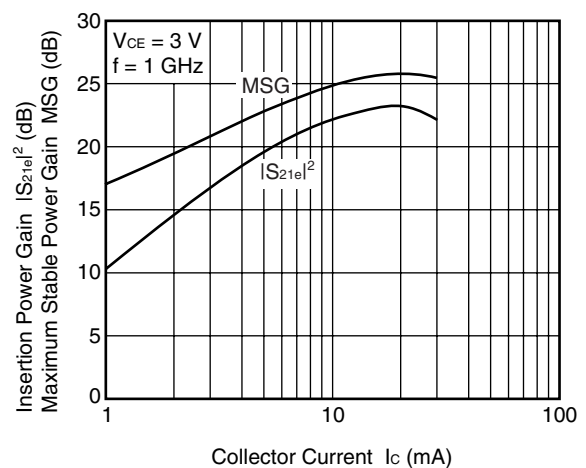
INSERTION POWER GAIN, MAG
vs. COLLECTOR CURRENT



INSERTION POWER GAIN, MSG
vs. COLLECTOR CURRENT

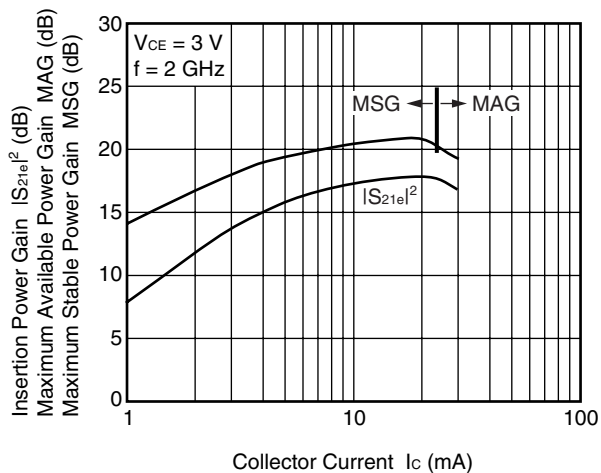


INSERTION POWER GAIN, MSG
vs. COLLECTOR CURRENT

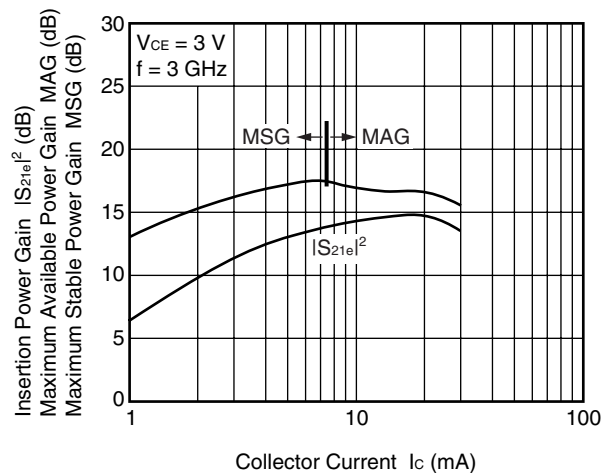


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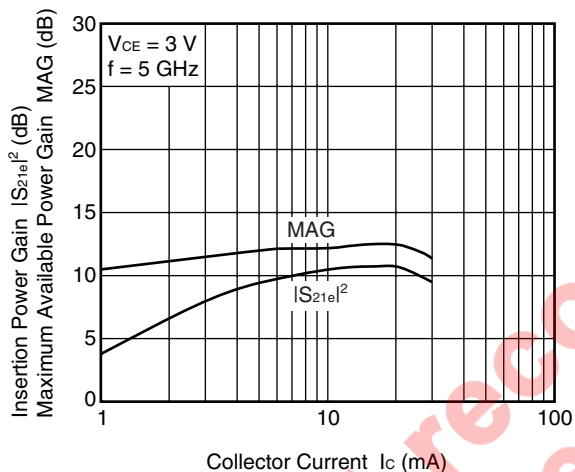
INSERTION POWER GAIN, MAG, MSG
vs. COLLECTOR CURRENT



INSERTION POWER GAIN, MAG, MSG
vs. COLLECTOR CURRENT

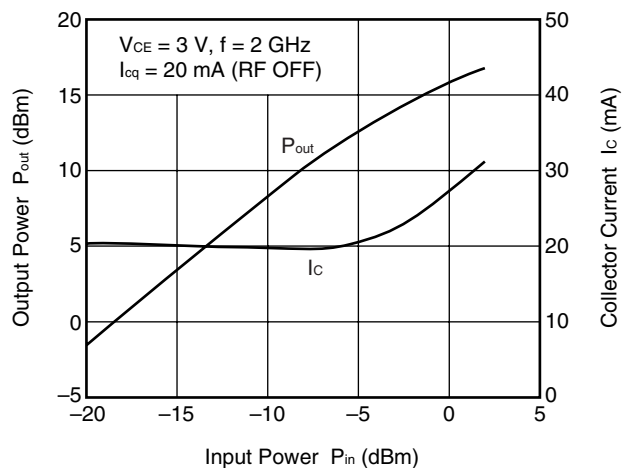


INSERTION POWER GAIN, MAG
vs. COLLECTOR CURRENT



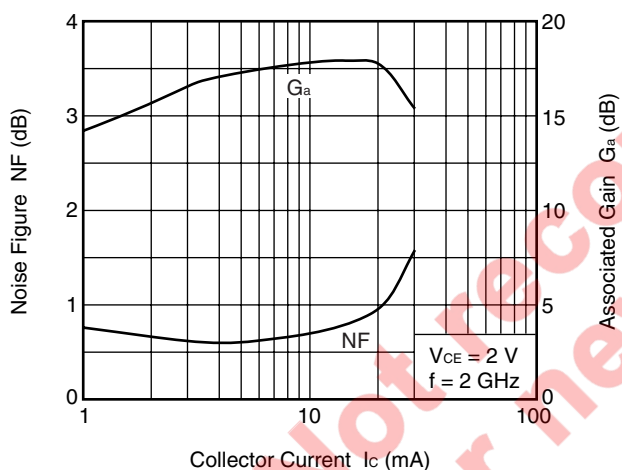
Remark The graphs indicate nominal characteristics.

OUTPUT POWER, COLLECTOR CURRENT vs. INPUT POWER



Measuring method : Measured at power matched with external sleeve tuner. (The load resistance is not inserted between the base DC power supply and Bias Tee.)

NOISE FIGURE, ASSOCIATED GAIN vs. COLLECTOR CURRENT



Remark The graphs indicate nominal characteristics.

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S-PARAMETERS

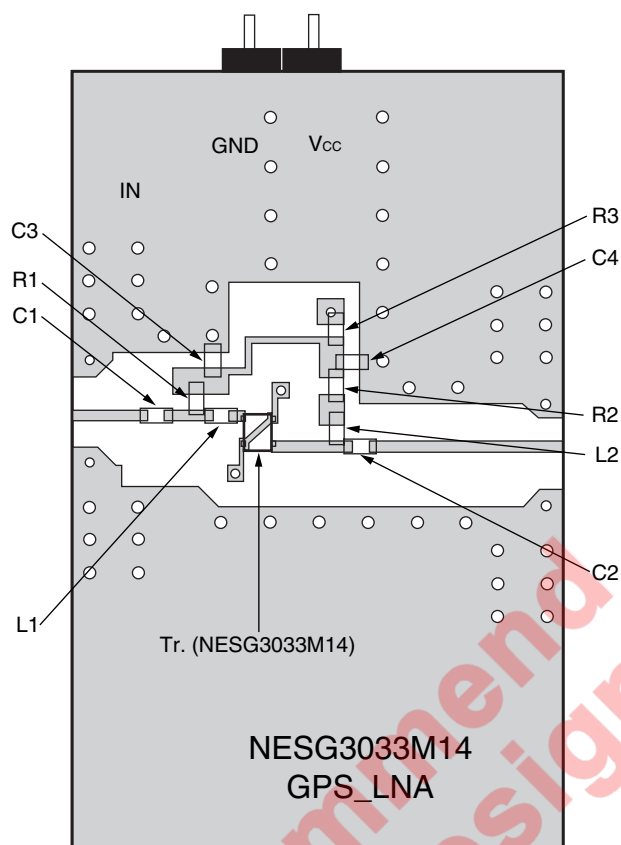
S-parameters and noise parameters are provided on our web site in a form (S2P) that enables direct import of the parameters to microwave circuit simulators without the need for keyboard inputs.

Click here to download S-parameters.

[Products] → [RF Devices] → [Device Parameters]

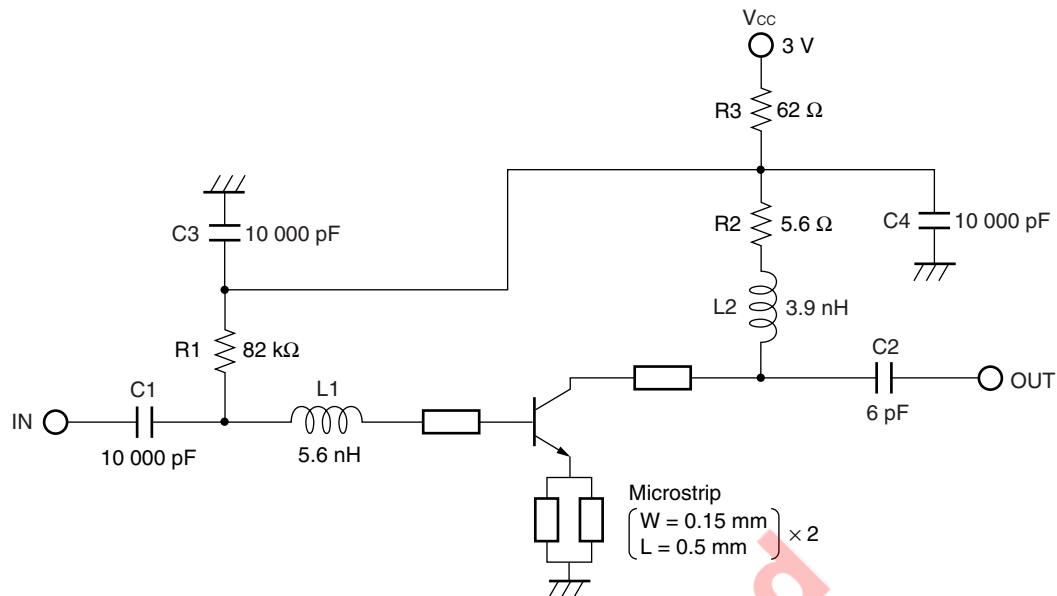
URL <http://www.renesas.com/products/microwave/>

EVALUATION CIRCUIT EXAMPLE (f = 1.575 GHz LNA)



- Notes**
1. 15 × 24 mm, t = 0.2 mm double sided copper clad glass epoxy PWB.
 2. Au plated on pattern
 3. ○ : Through holes

<R> EVALUATION CIRCUIT (f = 1.575 GHz LNA)



The application circuits and their parameters are for reference only and are not intended for use in actual design-ins.

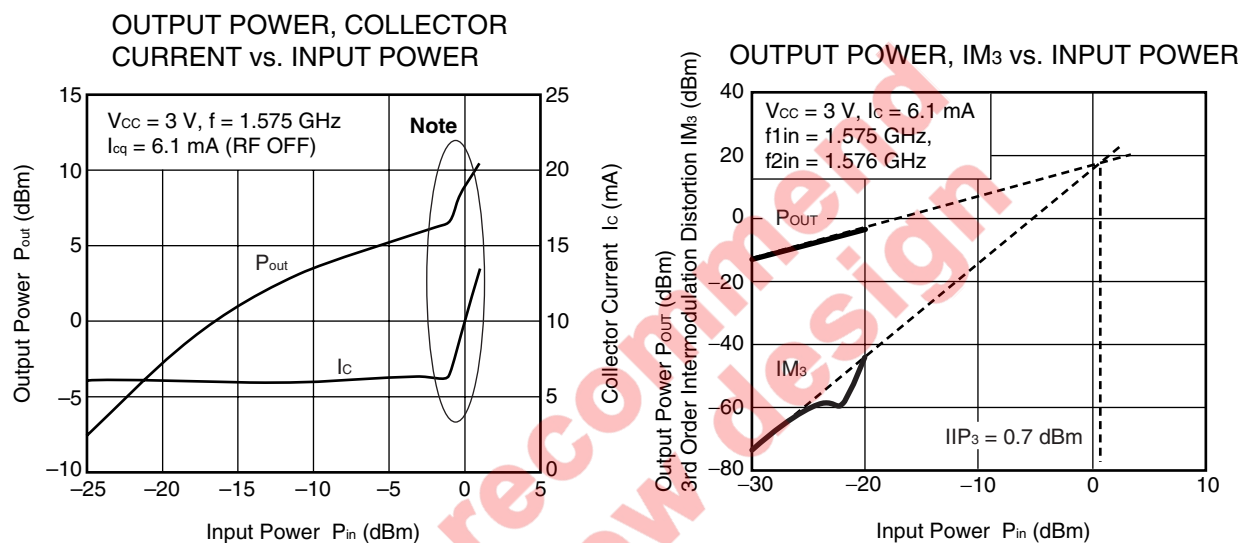
<R> COMPONENT LIST

Symbol	Parts	Part Number	Maker	Value
C1, C3, C4	Chip Capacitor	GRM155B31H103KA88	Murata	10 000 pF
C2	Chip Capacitor	GRM1552C1H6R0DZ01	Murata	6 pF
L1	Chip Inductor	AML1005H5N6STS	FDK	5.6 nH
L2	Chip Inductor	AML1005H3N9STS	FDK	3.9 nH
R1	Chip Resistor	MCR01MZPJ823	ROHM	82 kΩ
R2	Chip Resistor	MCR01MZPJ5R6	ROHM	5.6 Ω
R3	Chip Resistor	MCR01MZPJ620	ROHM	62 Ω

<R> EXAMPLE OF CHARACTERISTICS FOR 1.575 GHz LNA EVALUATION BOARD

ELECTRICAL CHARACTERISTICS ($T_A = +25^\circ\text{C}$, $V_{CC} = 3\text{ V}$, $I_C = 6.1\text{ mA}$, $f = 1.575\text{ GHz}$)

Parameter	Symbol	Value	Unit
Noise Figure	NF	0.72	dB
Gain	G_a	17.3	dB
Input Return Loss	RL_{in}	10.3	dB
Output Return Loss	RL_{out}	14.2	dB
Gain 1 dB Compression Output Power	$P_{O(1\text{ dB})}$	-0.3	dBm
Input 3rd Order Distortion Interception Point	IIP_3	0.7	dBm

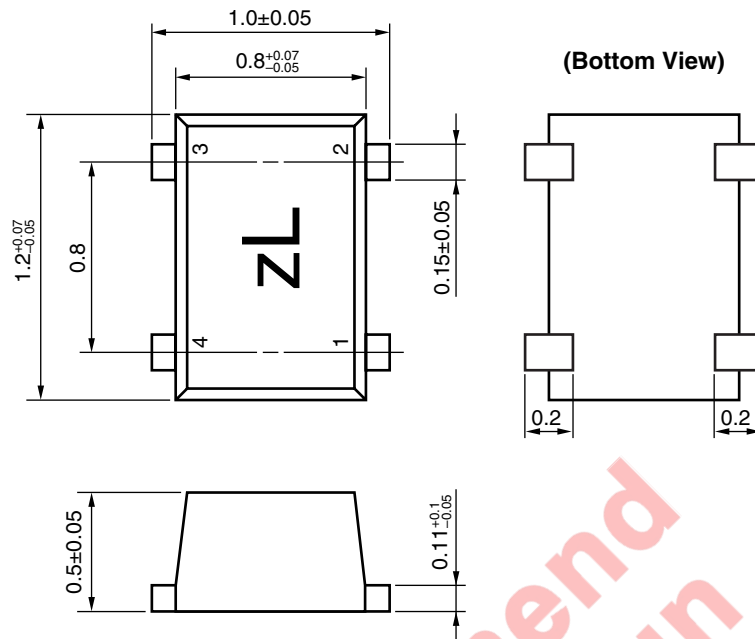
TYPICAL CHARACTERISTICS ($T_A = +25^\circ\text{C}$, unless otherwise specified)

Note A current increase is seen because the ESD protection element is turned on. However, there is no influence of deterioration etc. on reliability.

Remark The graph indicates nominal characteristics.

PACKAGE DIMENSIONS

<R> 4-PIN LEAD-LESS MINIMOLD (M14, 1208 PKG) (UNIT: mm)



PIN CONNECTIONS

1. Collector
2. Emitter
3. Base
4. NC (Connected with Pin 2) Note

Note A NC pin is Non-connection in the mold package (When NC-pin is open state, It will get an influences of floating capacitance. Therefore, we recommend that NC pin connect to Emitter pin).

Revision History	NESG3033M14 Data Sheet
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Rev.	Date	Description	
		Page	Summary
1.00	Jul 19, 2005	–	First edition issued
2.00	Sep 11, 2007	–	Second edition issued
3.00	Sep 14, 2012	Throughout	The company name is changed to Renesas Electronics Corporation.
		p.1	Modification of ORDERING INFORMATION
		p.3	Modification of ELECTRICAL CHARACTERISTICS
		p.3	Modification of h_{FE} CLASSIFICATION
		p.10	Modification of method for obtaining S-parameters
		p.12	Modification of EVALUTION CIRCUIT
		p.12	Modification of COMPONENT LIST
		p.13	Modification of EXAMPLE OF CHARACTERISTICS FOR $f = 1.575$ GHz LNA EVALUATION BOARD
		p.14	Modification of PACKAGE DIMENSIONS

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for new design

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